

GRADED COMPOSITION METAL OXIDE TUNNEL BARRIER INTERPOLY  
INSULATOR

Abstract of the Disclosure

- 5 Structures and methods for programmable array type logic and/or memory devices with graded composition metal oxide tunnel barrier intergate insulators are provided. The programmable array type logic and/or memory devices include a floating gate transistor. The floating gate has a first source/drain region and a second source/drain region separated by a channel region in a substrate. A floating
- 10 gate opposes the channel region and is separated therefrom by a gate oxide. A control gate opposes the floating gate and is separated from the floating gate by a compositionally graded mixed metal oxide tunnel barrier intergate insulator.